



## Dual N-Channel 30-V (D-S) MOSFET

### PRODUCT SUMMARY

| $V_{DS}$ (V) | $R_{DS(on)}$ ( $\Omega$ ) | $I_D$ (A) <sup>a</sup> | $Q_g$ (Typ.) |
|--------------|---------------------------|------------------------|--------------|
| 30           | 0.0235 at $V_{GS} = 10$ V | 8.5                    | 6.7          |
|              | 0.028 at $V_{GS} = 4.5$ V | 7.8                    |              |

### FEATURES

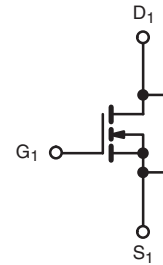
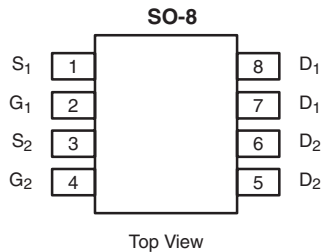
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFET
- 100 %  $R_g$  Tested
- 100 % UIS Tested
- Compliant to RoHS Directive 2002/95/EC



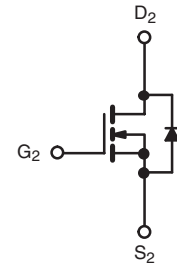
**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- PC System Power
- Low Current DC/DC



N-Channel MOSFET



N-Channel MOSFET

Ordering Information: Si4214DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

### ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$ , unless otherwise noted

| Parameter                                              | Symbol         | Limit                    | Unit             |
|--------------------------------------------------------|----------------|--------------------------|------------------|
| Drain-Source Voltage                                   | $V_{DS}$       | 30                       | V                |
| Gate-Source Voltage                                    | $V_{GS}$       | $\pm 20$                 |                  |
| Continuous Drain Current ( $T_J = 150^\circ\text{C}$ ) | $I_D$          | $T_C = 25^\circ\text{C}$ | A                |
|                                                        |                | $T_C = 70^\circ\text{C}$ |                  |
|                                                        |                | $T_A = 25^\circ\text{C}$ |                  |
|                                                        |                | $T_A = 70^\circ\text{C}$ |                  |
| Pulsed Drain Current                                   | $I_{DM}$       | 30                       | A                |
| Source-Drain Current Diode Current                     | $I_S$          | $T_C = 25^\circ\text{C}$ |                  |
|                                                        |                | $T_A = 25^\circ\text{C}$ |                  |
| Pulsed Source-Drain Current                            | $I_{SM}$       | 30                       |                  |
| Single Pulse Avalanche Current                         | $I_{AS}$       | 10                       | mJ               |
| Single Pulse Avalanche Energy                          | $E_{AS}$       | 5                        |                  |
| Maximum Power Dissipation                              | $P_D$          | $T_C = 25^\circ\text{C}$ | W                |
|                                                        |                | $T_C = 70^\circ\text{C}$ |                  |
|                                                        |                | $T_A = 25^\circ\text{C}$ |                  |
|                                                        |                | $T_A = 70^\circ\text{C}$ |                  |
| Operating Junction and Storage Temperature Range       | $T_J, T_{stg}$ | - 55 to 150              | $^\circ\text{C}$ |

### THERMAL RESISTANCE RATINGS

| Parameter                                   |               | Symbol     | Typ. | Max. | Unit               |
|---------------------------------------------|---------------|------------|------|------|--------------------|
| Maximum Junction-to-Ambient <sup>b, d</sup> | $t \leq 10$ s | $R_{thJA}$ | 52   | 62.5 | $^\circ\text{C/W}$ |
| Maximum Junction-to-Foot (Drain)            | Steady-State  | $R_{thJF}$ | 30   | 40   |                    |

Notes:

a. Based on  $T_C = 25^\circ\text{C}$ .

b. Surface Mounted on 1" x 1" FR4 board.

c.  $t = 10$  s.

d. Maximum under steady state conditions is  $110^\circ\text{C/W}$ .

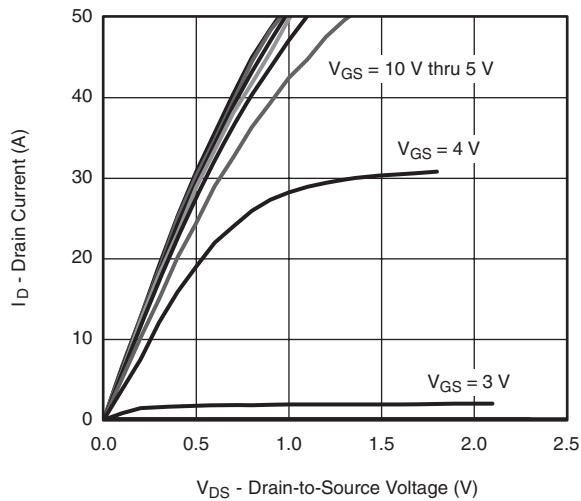
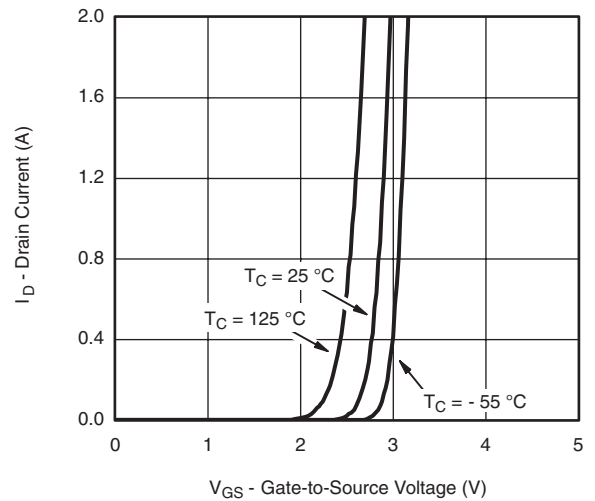
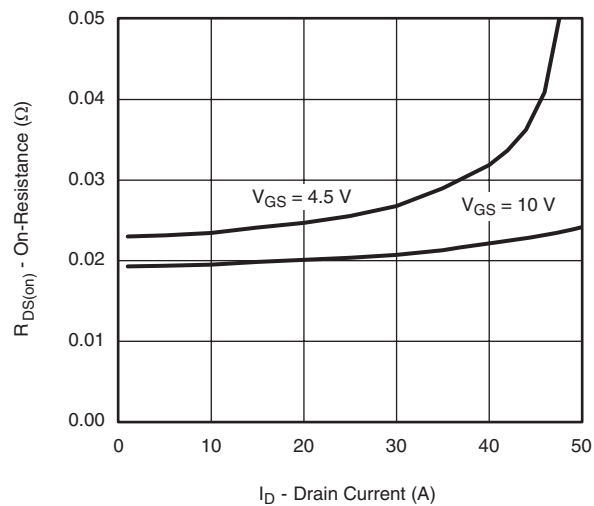
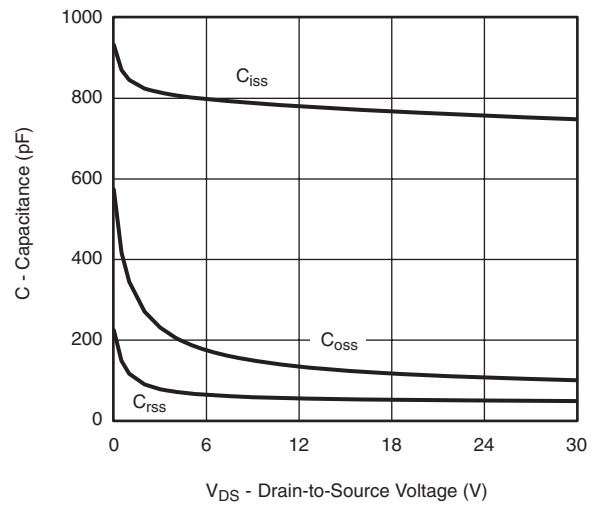
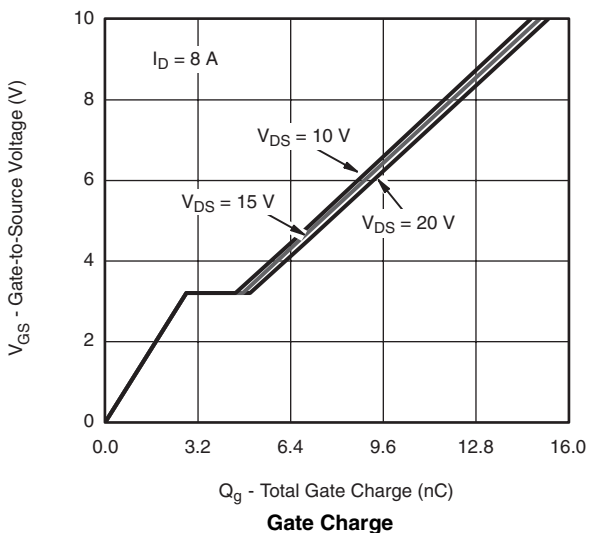
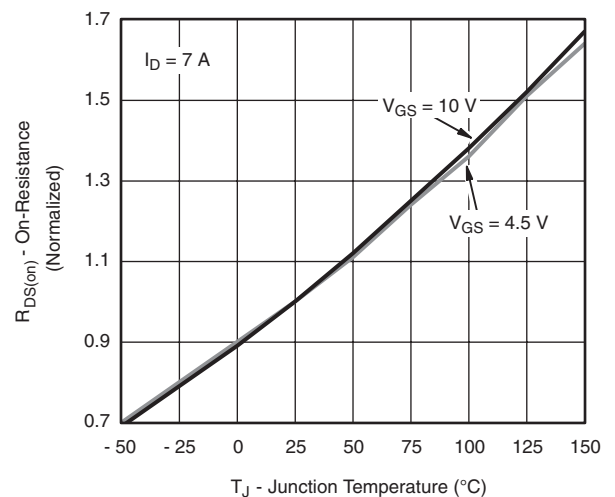
## Si4214DY

Vishay Siliconix



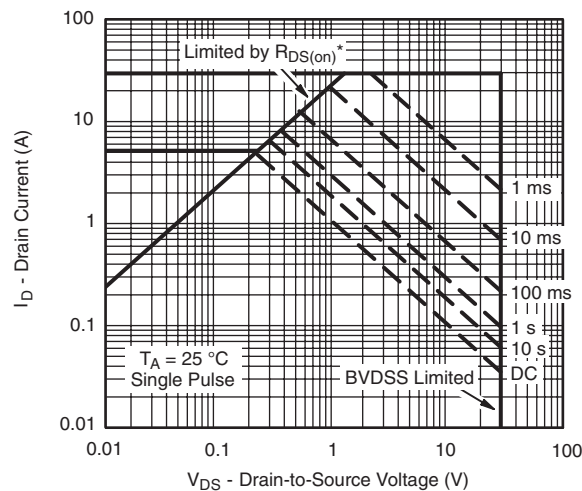
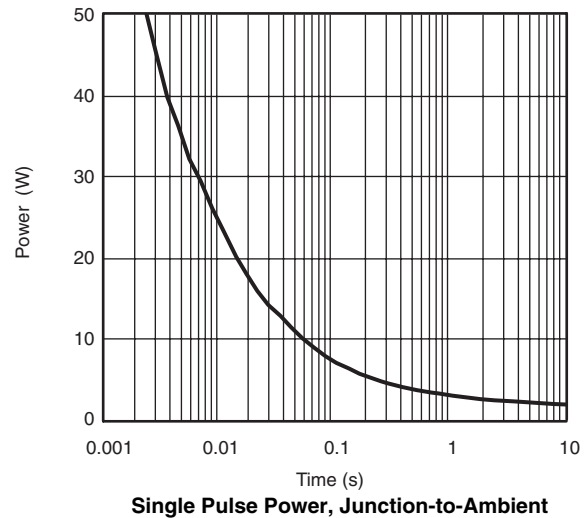
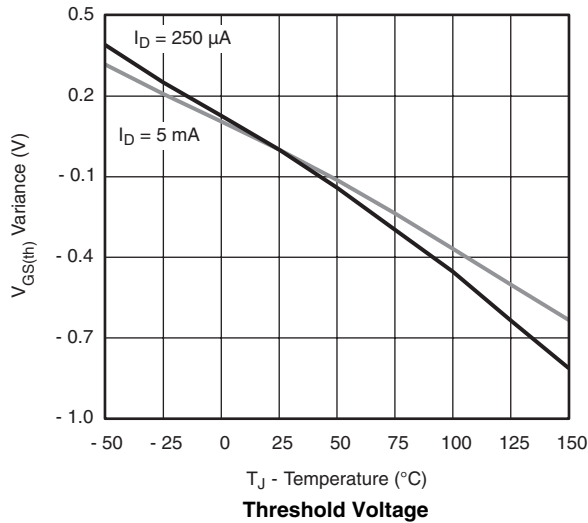
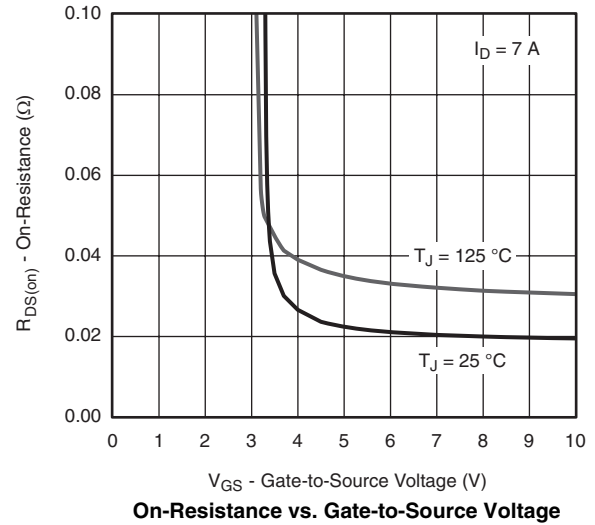
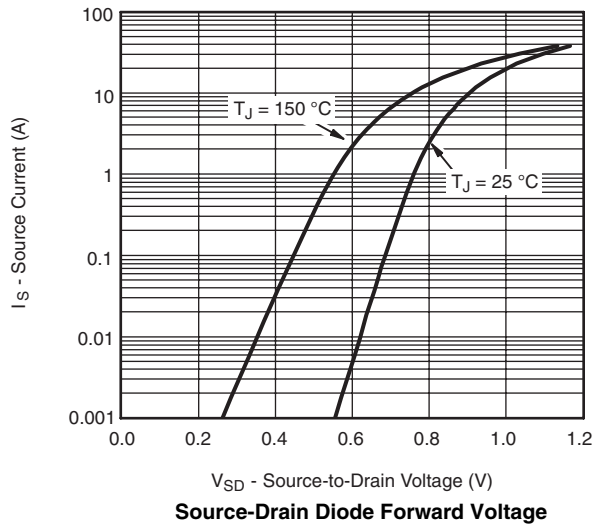
| SPECIFICATIONS T <sub>J</sub> = 25 °C, unless otherwise noted |                                      |                                                                                                                                   |      |        |        |       |
|---------------------------------------------------------------|--------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------|------|--------|--------|-------|
| Parameter                                                     | Symbol                               | Test Conditions                                                                                                                   | Min. | Typ.   | Max.   | Unit  |
| Static                                                        |                                      |                                                                                                                                   |      |        |        |       |
| Drain-Source Breakdown Voltage                                | V <sub>DS</sub>                      | V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA                                                                                    | 30   |        |        | V     |
| V <sub>DS</sub> Temperature Coefficient                       | ΔV <sub>DS</sub> /T <sub>J</sub>     | I <sub>D</sub> = 250 μA                                                                                                           |      | 3.5    |        | mV/°C |
| V <sub>GS(th)</sub> Temperature Coefficient                   | ΔV <sub>GS(th)</sub> /T <sub>J</sub> | I <sub>D</sub> = 250 μA                                                                                                           |      | - 6.2  |        |       |
| Gate Threshold Voltage                                        | V <sub>GS(th)</sub>                  | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA                                                                       | 1.2  |        | 2.5    | V     |
| Gate-Body Leakage                                             | I <sub>GSS</sub>                     | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V                                                                                   |      |        | 100    | nA    |
| Zero Gate Voltage Drain Current                               | I <sub>DSS</sub>                     | V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V                                                                                     |      |        | 1      | μA    |
|                                                               |                                      | V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C                                                             |      |        | 10     |       |
| On -State Drain Current <sup>b</sup>                          | I <sub>D(on)</sub>                   | V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V                                                                                     | 20   |        |        | A     |
| Drain-Source On-State Resistance <sup>b</sup>                 | R <sub>DS(on)</sub>                  | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 7 A                                                                                      |      | 0.0195 | 0.0235 | Ω     |
|                                                               |                                      | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 5 A                                                                                     |      | 0.023  | 0.028  |       |
| Forward Transconductance <sup>b</sup>                         | g <sub>fs</sub>                      | V <sub>DS</sub> = 15 V, I <sub>D</sub> = 7 A                                                                                      |      | 35     |        | S     |
| Dynamic <sup>a</sup>                                          |                                      |                                                                                                                                   |      |        |        |       |
| Input Capacitance                                             | C <sub>iss</sub>                     | N-Channel<br>V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V, I <sub>D</sub> = 1 MHz                                                |      | 785    |        | pF    |
| Output Capacitance                                            | C <sub>oss</sub>                     |                                                                                                                                   |      | 125    |        |       |
| Reverse Transfer Capacitance                                  | C <sub>rss</sub>                     |                                                                                                                                   |      | 53     |        |       |
| Total Gate Charge                                             | Q <sub>g</sub>                       | V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 8 A                                                              |      | 15     | 23     | nC    |
|                                                               |                                      | N-Channel<br>V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 8 A                                                |      | 6.7    | 10.5   |       |
| Q <sub>gs</sub>                                               |                                      |                                                                                                                                   | 2.8  |        |        |       |
| Q <sub>gd</sub>                                               |                                      |                                                                                                                                   | 2.0  |        |        |       |
| Gate Resistance                                               | R <sub>g</sub>                       | f = 1 MHz                                                                                                                         | 0.4  | 2.1    | 4.2    |       |
| Turn-On Delay Time                                            | t <sub>d(on)</sub>                   | N-Channel<br>V <sub>DD</sub> = 15 V, R <sub>L</sub> = 3 Ω<br>I <sub>D</sub> ≅ 5 A, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 1 Ω |      | 13     | 25     | ns    |
| Rise Time                                                     | t <sub>r</sub>                       |                                                                                                                                   |      | 11     | 22     |       |
| Turn-Off Delay Time                                           | t <sub>d(off)</sub>                  |                                                                                                                                   |      | 18     | 35     |       |
| Fall Time                                                     | t <sub>f</sub>                       |                                                                                                                                   |      | 9      | 18     |       |
| Turn-On Delay Time                                            | t <sub>d(on)</sub>                   | N-Channel<br>V <sub>DD</sub> = 15 V, R <sub>L</sub> = 3 Ω<br>I <sub>D</sub> ≅ 5 A, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 1 Ω |      | 7      | 14     |       |
| Rise Time                                                     | t <sub>r</sub>                       |                                                                                                                                   |      | 9      | 18     |       |
| Turn-Off Delay Time                                           | t <sub>d(off)</sub>                  |                                                                                                                                   |      | 16     | 30     |       |
| Fall Time                                                     | t <sub>f</sub>                       |                                                                                                                                   |      | 8      | 16     |       |
| Drain-Source Body Diode Characteristics                       |                                      |                                                                                                                                   |      |        |        |       |
| Continuous Source-Drain Diode Current                         | I <sub>S</sub>                       | T <sub>C</sub> = 25 °C                                                                                                            |      |        | 2.8    | A     |
| Pulse Diode Forward Current <sup>a</sup>                      | I <sub>SM</sub>                      |                                                                                                                                   |      |        | 30     |       |
| Body Diode Voltage                                            | V <sub>SD</sub>                      | I <sub>S</sub> = 1.8 A                                                                                                            |      | 0.77   | 1.1    | V     |
| Body Diode Reverse Recovery Time                              | t <sub>rr</sub>                      | N-Channel<br>I <sub>F</sub> = 2.2 A, dI/dt = 100 A/μs, T <sub>J</sub> = 25 °C                                                     |      | 35     | 60     | ns    |
| Body Diode Reverse Recovery Charge                            | Q <sub>rr</sub>                      |                                                                                                                                   |      | 40     | 70     | nC    |
| Reverse Recovery Fall Time                                    | t <sub>a</sub>                       |                                                                                                                                   |      | 19     |        | nS    |
| Reverse Recovery Rise Time                                    | t <sub>b</sub>                       |                                                                                                                                   |      | 16     |        |       |

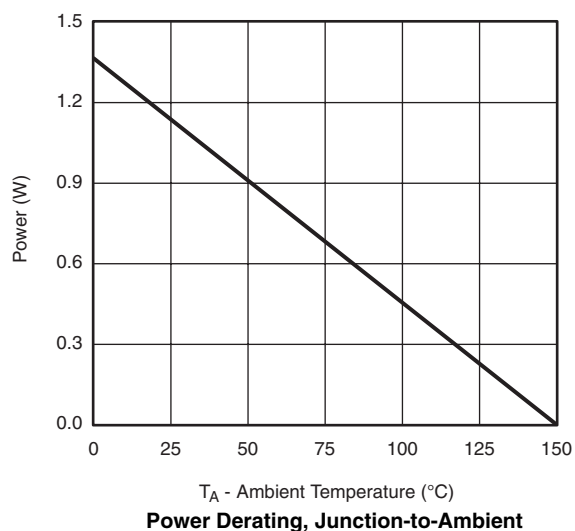
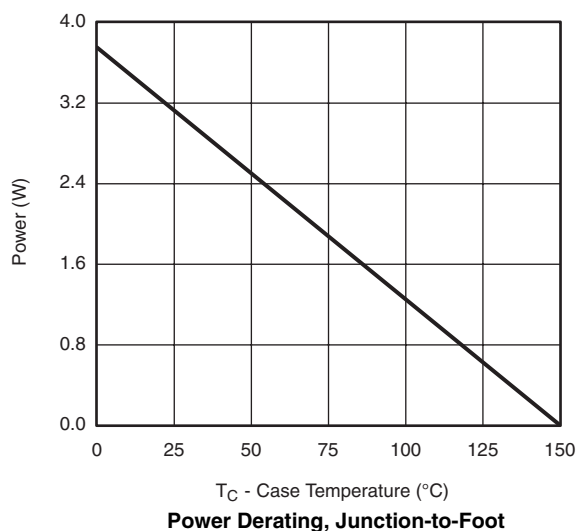
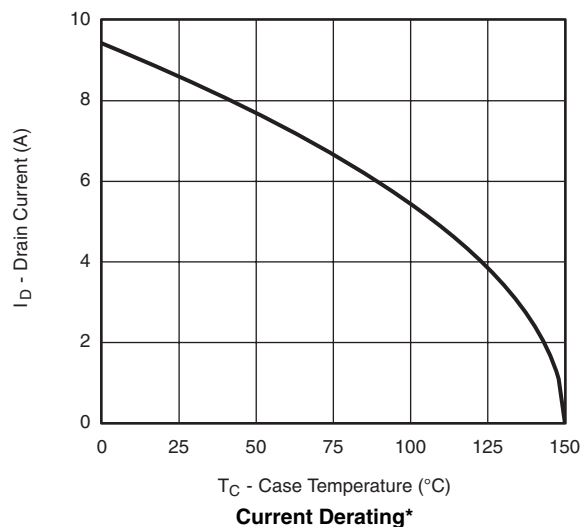
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.


**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

**Output Characteristics**

**Transfer Characteristics**

**On-Resistance vs. Drain Current and Gate Voltage**

**Capacitance**

**Gate Charge**

**On-Resistance vs. Junction Temperature**

## Si4214DY

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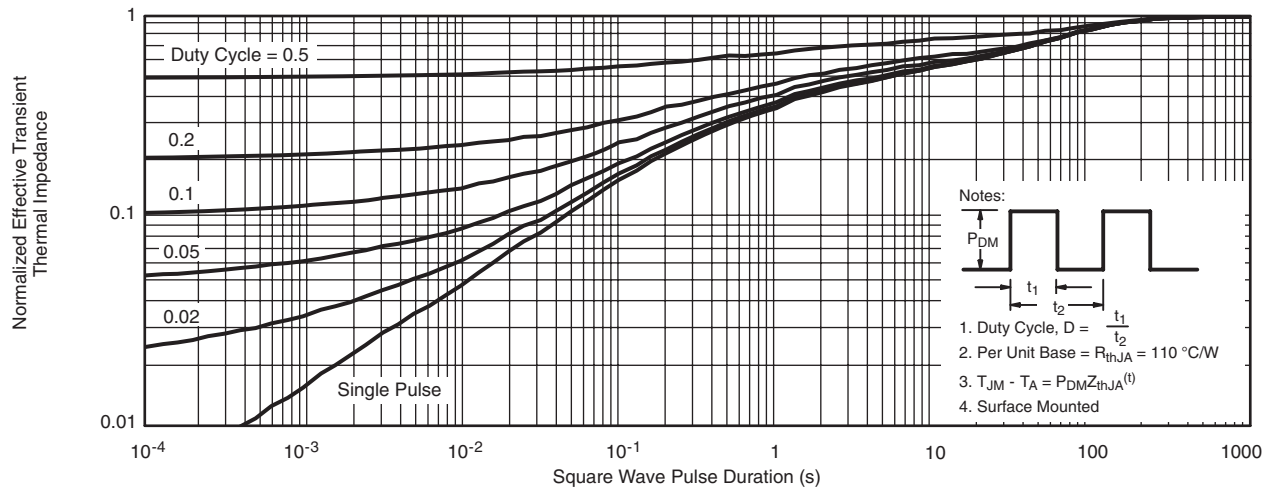
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified**Safe Operating Area, Junction-to-Ambient**


**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted


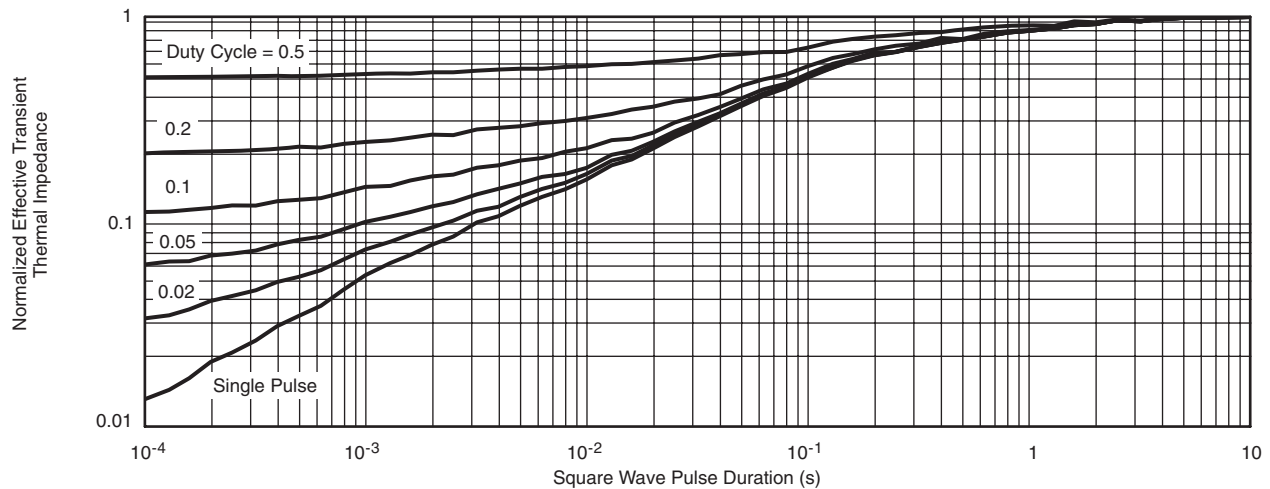
\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

## Si4214DY

Vishay Siliconix

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?64726](http://www.vishay.com/ppg?64726).

## SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



| DIM                            | MILLIMETERS |      | INCHES    |       |
|--------------------------------|-------------|------|-----------|-------|
|                                | Min         | Max  | Min       | Max   |
| A                              | 1.35        | 1.75 | 0.053     | 0.069 |
| A <sub>1</sub>                 | 0.10        | 0.20 | 0.004     | 0.008 |
| B                              | 0.35        | 0.51 | 0.014     | 0.020 |
| C                              | 0.19        | 0.25 | 0.0075    | 0.010 |
| D                              | 4.80        | 5.00 | 0.189     | 0.196 |
| E                              | 3.80        | 4.00 | 0.150     | 0.157 |
| e                              | 1.27 BSC    |      | 0.050 BSC |       |
| H                              | 5.80        | 6.20 | 0.228     | 0.244 |
| h                              | 0.25        | 0.50 | 0.010     | 0.020 |
| L                              | 0.50        | 0.93 | 0.020     | 0.037 |
| q                              | 0°          | 8°   | 0°        | 8°    |
| S                              | 0.44        | 0.64 | 0.018     | 0.026 |
| ECN: C-06527-Rev. I, 11-Sep-06 |             |      |           |       |
| DWG: 5498                      |             |      |           |       |

## RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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